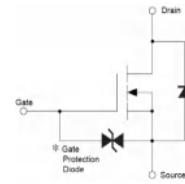




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2SK3019KT Plastic-Encapsulate MOSFETS

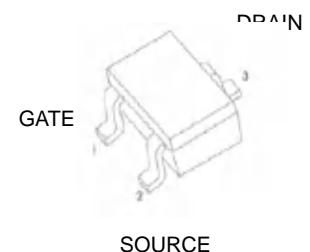
$V_{(BR)DSS}$	$R_{DS(on)}\text{MAX}$	I_D
30 V	8Ω@4V	100mA
	13Ω@2.5V	



FEATURE

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Easily designed drive circuits
- Easy to parallel

Marking: KN



SOT-523

MOSFET MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{ds}	Drain-Source Voltage	30	V
V_{gs}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	0.1	A
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	833	$^\circ\text{C}/\text{W}$
P_D	Power Dissipation	0.15	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$



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MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0V, I_D = 10\mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$		1		μA
Gate –Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 2	μA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = 3V, I_D = 100\mu\text{A}$	0.8		1.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4V, I_D = 10\text{mA}$			8	Ω
		$V_{GS} = 2.5V, I_D = 1\text{mA}$			13	Ω
Forward Transconductance	g_{FS}	$V_{DS} = 3V, I_D = 10\text{mA}$	20			mS
Dynamic Characteristics*						
Input Capacitance	C_{iss}	$V_{DS} = 5V, V_{GS} = 0V, f = 1\text{MHz}$		13		pF
Output Capacitance	C_{oss}			9		pF
Reverse Transfer Capacitance	C_{rss}			4		pF
Switching Characteristics*						
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 5V, V_{DD} = 5V,$ $I_D = 10\text{mA}, R_g = 10\Omega, R_L = 500\Omega,$		15		ns
Rise Time	t_r			35		ns
Turn-Off Delay Time	$t_{d(off)}$			80		ns
Fall Time	t_f			80		ns

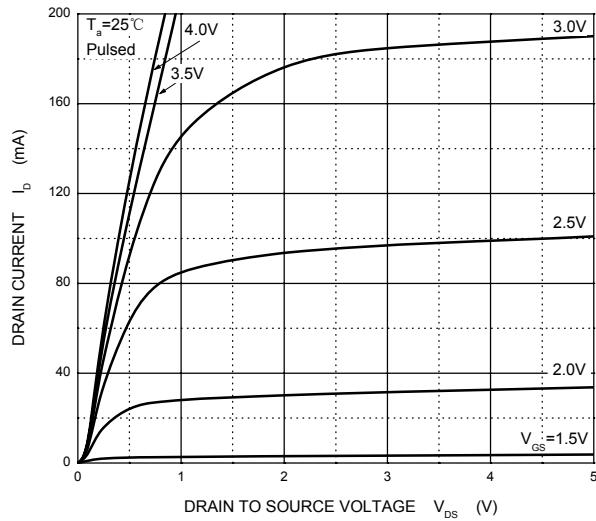
* These parameters have no way to verify.



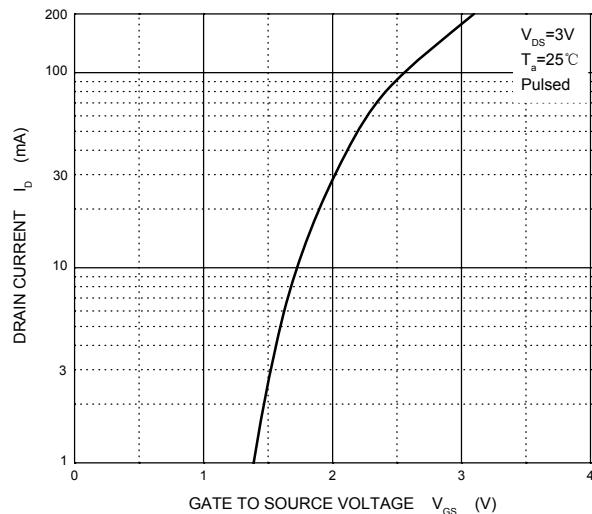
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Typical Characteristics

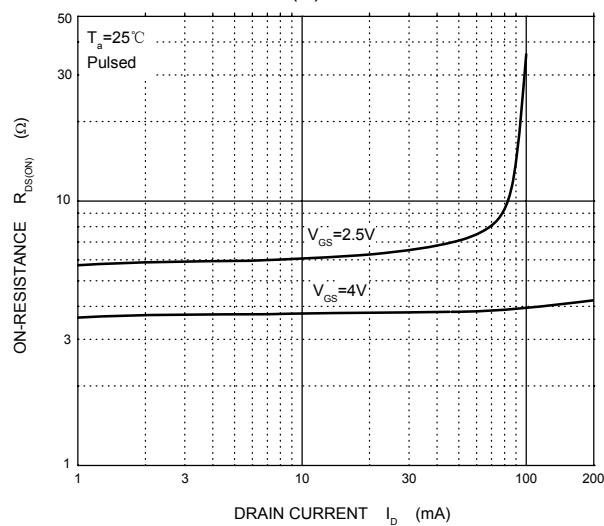
Output Characteristics



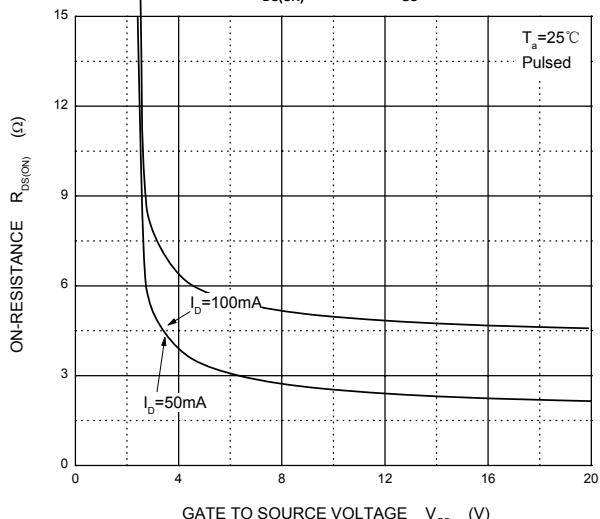
Transfer Characteristics



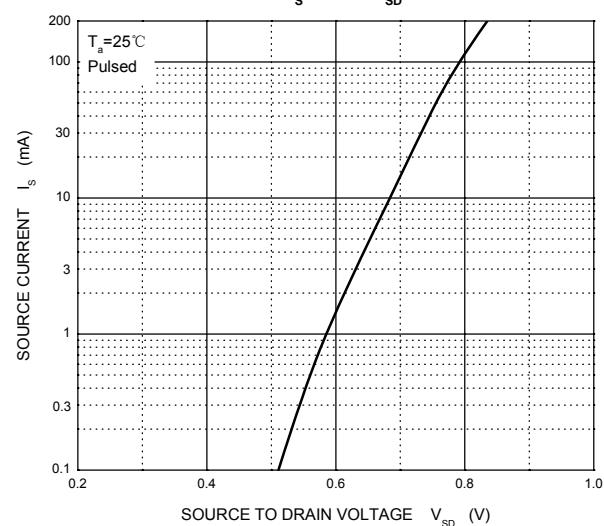
$R_{DS(ON)}$ —— I_D



$R_{DS(ON)}$ —— V_{GS}



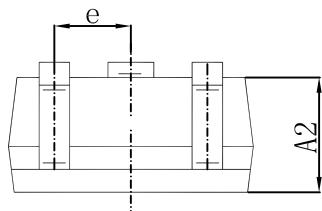
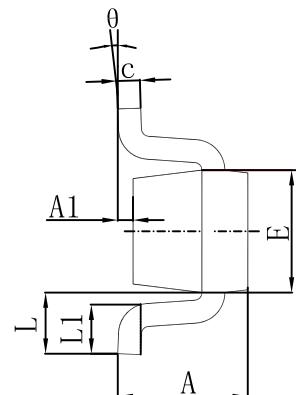
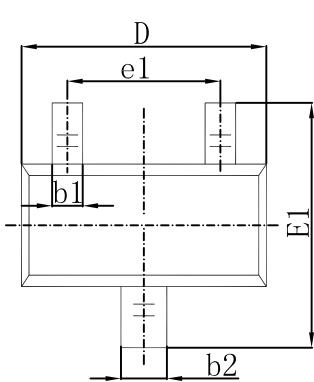
I_s —— V_{SD}





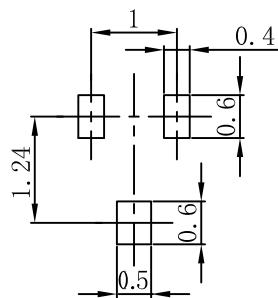
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SOT-523 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-523 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.